

IN THE CLAIMS:

Claims 1 through 4 have been amended herein, and claims 30 through 32 have been newly added herein. Please note that all claims currently pending and under consideration in the referenced application are shown below. Please enter these claims as amended. This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1. (Currently amended) A system for selectively depositing a material on a previously formed workpiece, comprising:
~~a platform for supporting sized and configured to support the workpiece, the workpiece including at least one semiconductor die during die, during a deposition process;~~
~~a deposition system configured to deposit at least one layer of unconsolidated material on the workpiece to a specific thickness; and~~
~~a sensing system configured to substantially simultaneously measure over the semiconductor die both measure a level of an upper surface of the workpiece and a surface level of a-the at least one layer of unconsolidated material previously deposited thereon, the sensing system further configured to continuously directly measure in a dimension substantially orthogonal to the platform a surface level during material deposition of the material on the upper surface according to direct measurements in the dimension substantially orthogonal to the platform until the surface level of the material is directly measured to be the specific thickness; and~~
~~a selective material consolidation system configured to at least partially consolidate a selected portion of the at least one layer of unconsolidated material.~~

2. (Currently amended) The system of claim 1, wherein the deposition system is comprises a spin-coating deposition system.

3. (Currently amended) The system of claim 2, wherein the sensing system includes

at least one sensor for positioned and configured to both measure measuring the upper surface of the workpiece and monitor for monitoring the surface level of the material deposited on the upper surface of the workpiece.

4. (Currently amended) The system of claim 2, wherein the sensing system includes a first sensor positioned and configured to measure for measuring the upper surface of the workpiece and a second sensor positioned and configured to monitor for monitoring the surface level of the material deposited on the upper surface of the workpiece.

5-7. (Canceled).

8. (Previously presented) The system of claim 1, wherein the workpiece is a semiconductor wafer.

9-29. (Canceled).

30. (New - Withdrawn) The system of claim 1, wherein the deposition system comprises a stereolithographic deposition system.

31. (New - Withdrawn) The system of claim 30, wherein the sensing system includes at least one sensor positioned and configured to both measure the upper surface of the workpiece and to monitor the surface level of the material deposited on the upper surface of the workpiece.

32. (New - Withdrawn) The system of claim 30, wherein the sensing system includes a first sensor positioned and configured to measure the upper surface of the workpiece and a second sensor positioned and configured to monitor the surface level of the material deposited on the upper surface of the workpiece.